UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/711,486	09/21/2004	James S. Dunn	BUR920040097US1	5485	
45601 7590 SCHLLV SCOTT		CD	EXAMINER		
400 GARDEN CIT			SU C		
GARDEN CITY, 1	NY 11530		ART UNIT PAPER NUMBER		
			2823		
SHORTENED STATUTORY PI	ERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE		
2 MONTI	HS	01/03/2007	PAPER		

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

			9
	Application No.	Applicant(s)	
	10/711,486	DUNN ET AL.	
Office Action Summary	Examiner	Art Unit	
	Su C. Kim	2823	
The MAILING DATE of this communication apperiod for Reply	ppears on the cover sheet w	ith the correspondence addre	ess
A SHORTENED STATUTORY PERIOD FOR REP WHICHEVER IS LONGER, FROM THE MAILING - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory perio - Failure to reply within the set or extended period for reply will, by statu Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNI 1.136(a). In no event, however, may a od will apply and will expire SIX (6) MON oute, cause the application to become Al	CATION. reply be timely filed NTHS from the mailing date of this common bandoned (35 U.S.C. § 133).	·
Status			
1) Responsive to communication(s) filed on 18	October 2006.		
2a) This action is FINAL. 2b) Th	nis action is non-final.		
3) Since this application is in condition for allow	ance except for formal mat	ters, prosecution as to the m	nerits is
closed in accordance with the practice under	Ex parte Quayle, 1935 C.E). 11, 453 O.G. 213.	
Disposition of Claims			
4)⊠ Claim(s) <u>1-26</u> is/are pending in the application	on.		
4a) Of the above claim(s) <u>18-23,25 and 26</u> is		eration.	
5) Claim(s) 1-17 and 24 is/are allowed.			
6) Claim(s) is/are rejected.			
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction and	/or election requirement.		
Application Papers			
9) The specification is objected to by the Examin	ner.		
10)⊠ The drawing(s) filed on <u>21 September 2006</u> is	·	☑ objected to by the Examir	ner.
Applicant may not request that any objection to th	•		
Replacement drawing sheet(s) including the corre	ection is required if the drawing	y(s) is objected to. See 37 CFR	1.121(d).
11) The oath or declaration is objected to by the I	Examiner. Note the attache	d Office Action or form PTO	-152.
Priority under 35 U.S.C. § 119			
12) ☐ Acknowledgment is made of a claim for foreignal ☐ All b) ☐ Some * c) ☐ None of:	gn priority under 35 U.S.C. §	§ 119(a)-(d) or (f).	
1. Certified copies of the priority docume	nts have been received.		
2. Certified copies of the priority docume	nts have been received in A	Application No	
3. Copies of the certified copies of the pri	iority documents have been	received in this National St	age
application from the International Bure	au (PCT Rule 17.2(a)).		
* See the attached detailed Office action for a list	st of the certified copies not	received.	
		HSIEN-MING LEE PRIMARY EXAMINE	B
Attachment(s)		V /	1.11
Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO/SB/08)	Paper No(Summary (PTO-413) (s)/Mail Date Informal Patent Application	6/06
Paper No(s)/Mail Date	6) Other:	• •	

Art Unit: 2823

DETAILED ACTION

Election/Restrictions

1. Claims 18-23 & 25 are withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected specie, there being no allowable generic or linking claim. Election was made **without** traverse in the reply filed on 10/18/2006.

Applicant's election without traverse of species I (Clams 1-17 and 24) in the reply filed on 10/18/2006 is acknowledged.

Drawings

2. The drawings are objected to under 37 CFR 1.83(a). The drawings must show every feature of the invention specified in the claims. Therefore, the "base layer is monocrystalline over the collector and polycrystalline over the trench isolation regions" claimed in claim 1, lines 4-5 must be shown or the feature(s) canceled from the claim(s). No new matter should be entered.

Corrected drawing sheets in compliance with 37 CFR 1.121(d) are required in reply to the Office action to avoid abandonment of the application. Any amended replacement drawing sheet should include all of the figures appearing on the immediate prior version of the sheet, even if only one figure is being amended. The figure or figure number of an amended drawing should not be labeled as "amended." If a drawing figure is to be canceled, the appropriate figure must be removed from the replacement sheet, and where necessary, the remaining figures must be renumbered and appropriate changes made to the brief description of the several views of the drawings for

Art Unit: 2823

consistency. Additional replacement sheets may be necessary to show the renumbering of the remaining figures. Each drawing sheet submitted after the filing date of an application must be labeled in the top margin as either "Replacement Sheet" or "New Sheet" pursuant to 37 CFR 1.121(d). If the changes are not accepted by the examiner, the applicant will be notified and informed of any required corrective action in the next Office action. The objection to the drawings will not be held in abeyance.

Allowable Subject Matter

3. Claims 1-17 and 24 allowed over prior art.

Pertaining claims 1 & 24, Burghartz et al. (US 5059544) discloses forming a pedestal atop structure that is comprising at lease base layer (Fig. 5, 18, 21, 22) located on a surface of substrate (Fig. 4, 12) having a collector and trench isolation regions (16) located therein, wherein said base layer is monocrystalline (single crystalline silicon 20) over the collector and polycrystalline (22) over the trench isolation regions; Forming an extra base layer over said structure (Fig. 4, 31 & 24) including pedestal wherein said extra base layer comprising monocrystalline material (34) over the substrate and polycrystalline material over the pedestal (Fig. 7, 52) and said base layer that is polycrystalline, said polycrystalline material over said pedestal is thinner than the polycrystalline material over said base layer that is polycrystalline (Fig. 7, thickness of 52 is thinner than the thickness of polysilicon 18)

Art Unit: 2823

However, Burghartz fails to teach converting at least said polycrystalline material over said pedestal of said extra base layer into an oxide utilizing a low temperature process that is performed at a temperature of about 700°C or less; removing said oxide and said pedestal from said structure to provide an emitter opening; and

forming at least a polysilicon emitter in said emitter opening.

Reasons for Allowance

4. The following is a statement of reasons for the indication of allowable subject matter:

After further search and consideration it is determined that the prior art of record neither anticipated nor renders obvious the claimed subject matter of the instant application as a whole either taken alone or in combination, in particular, prior art of record does not teach "converting at least said polycrystalline material over said pedestal of said extra base layer into an oxide utilizing a low temperature process that is performed at a temperature of about 700°C or less;

removing said oxide and said pedestal from said structure to provide an emitter opening; and

forming at least a polysilicon emitter in said emitter opening" as recited in claim 1 and "converting at least said polycrystalline material over said oxide pedestal of said extra base layer into an oxide utilizing a low temperature oxidation process;

Art Unit: 2823

removing said oxide and said oxide pedestal from said structure using a single etching process to provide an emitter opening;

forming an oxide layer on exposed surfaces using a second low temperature oxidation process;

forming a nitride spacer within said opening;

removing said oxide layer from a bottom surface of said emitter opening exposing said base layer; and

forming at least a polysilicon emitter in said emitter opening" as recited in claim 24

Claims 2-17 are also allowed as being directly or indirectly dependent of the allowed base claim(s).

Conclusion

This application is in condition for allowance except for the following formal matters:

Drawing objection on paragraph 2

Prosecution on the merits is closed in accordance with the practice under *Ex* parte Quayle, 1935 C.D. 11, 453 O.G. 213.

A shortened statutory period for reply to this action is set to expire **TWO MONTHS** from the mailing date of this letter.

Art Unit: 2823

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Su C. Kim whose telephone number is (571) 272-5972. The examiner can normally be reached on Monday - Thursday, 9:00AM to 7:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on (571) 272-1907. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Su C. Kim 12/19/2006

HSIEN-MING LES PRIMARY EXAMPLER